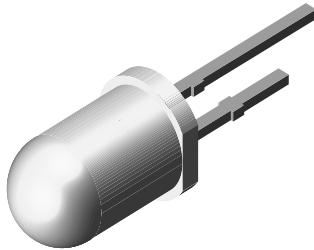


Infrared Emitting Diode, 950 nm, GaAs



94 8390

DESCRIPTION

TSUS5200 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue-gray tinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- Angle of half intensity: $\varphi = \pm 15^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- Emitter in reflective sensors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSUS5200	20	± 15	950	800
TSUS5201	25	± 15	950	800
TSUS5202	30	± 15	950	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS5200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSUS5201	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSUS5202	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	150	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	300	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	2.5	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

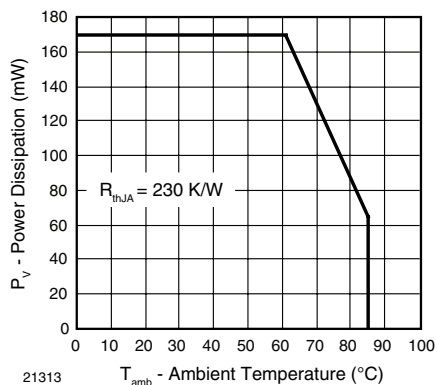


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

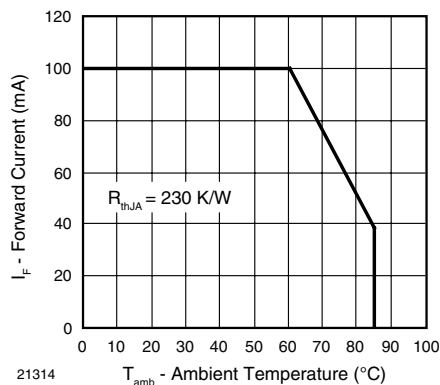


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.3	1.7	V
Temperature coefficient of V _F	I _F = 100 mA	TK _{V_F}		- 1.3		mV/K
Reverse current	V _R = 5 V	I _R			100	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		30		pF
Temperature coefficient of φ _e	I _F = 20 mA	TKφ _e		- 0.8		%/K
Angle of half intensity		φ		± 15		deg
Peak wavelength	I _F = 100 mA	λ _p		950		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ _p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1.5 A	t _r		400		ns
Fall time	I _F = 100 mA	t _f		800		ns
	I _F = 1.5 A	t _f		400		ns
Virtual source diameter		d		3.8		mm

Note

T_{amb} = 25 °C, unless otherwise specified



TSUS5200, TSUS5201, TSUS5202

Infrared Emitting Diode, 950 nm, GaAs Vishay Semiconductors

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 1.5 \text{ A}$, $t_p = 100 \mu\text{s}$	TSUS5200	V_F		2.2	3.4	V
		TSUS5201	V_F		2.2	3.4	V
		TSUS5202	V_F		2.2	2.7	V
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSUS5200	I_e	10	20	50	mW/sr
		TSUS5201	I_e	15	25	50	mW/sr
		TSUS5202	I_e	20	30	50	mW/sr
	$I_F = 1.5 \text{ A}$, $t_p = 100 \mu\text{s}$	TSUS5200	I_e	95	180		mW/sr
		TSUS5201	I_e	120	230		mW/sr
		TSUS5202	I_e	170	280		mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSUS5200	ϕ_e		13		mW
		TSUS5201	ϕ_e		14		mW
		TSUS5202	ϕ_e		15		mW

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

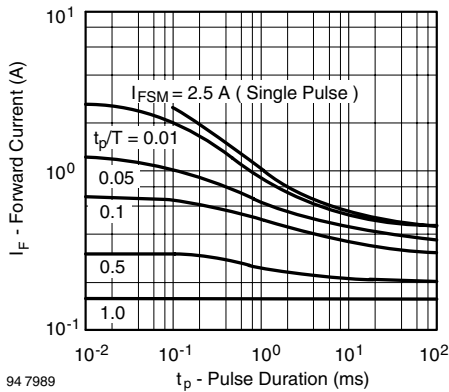


Fig. 3 - Pulse Forward Current vs. Pulse Duration

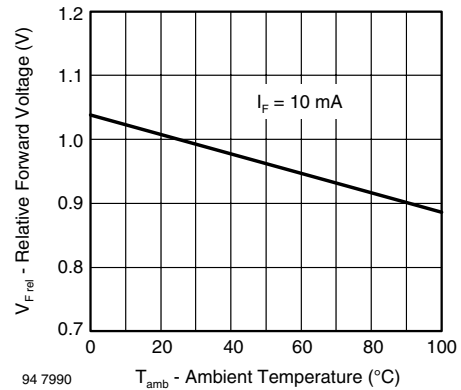


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

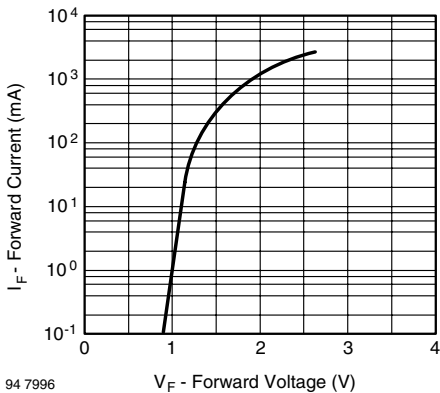


Fig. 4 - Forward Current vs. Forward Voltage

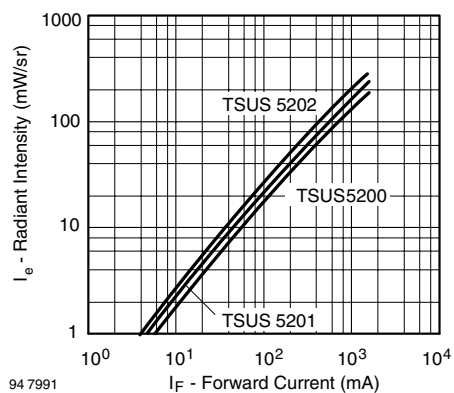


Fig. 6 - Radiant Intensity vs. Forward Current

TSUS5200, TSUS5201, TSUS5202



Vishay Semiconductors Infrared Emitting Diode, 950 nm, GaAs

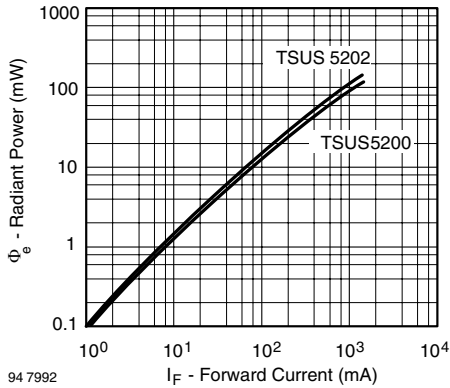


Fig. 7 - Radiant Power vs. Forward Current

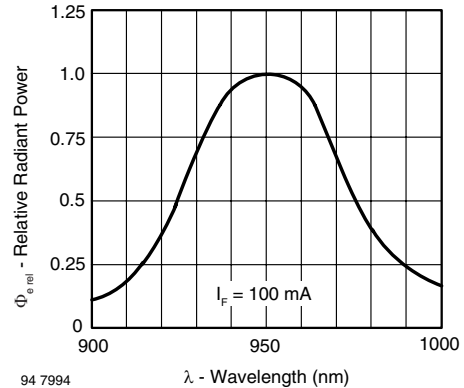


Fig. 9 - Relative Radiant Power vs. Wavelength

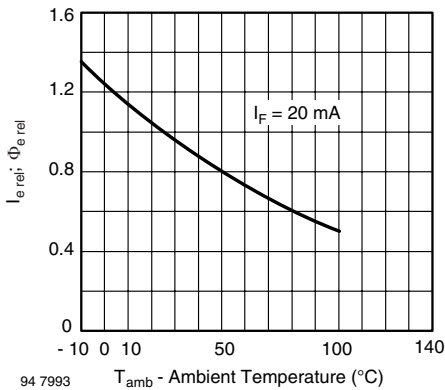


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

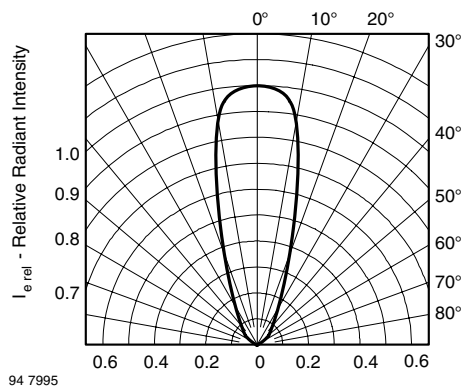
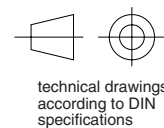
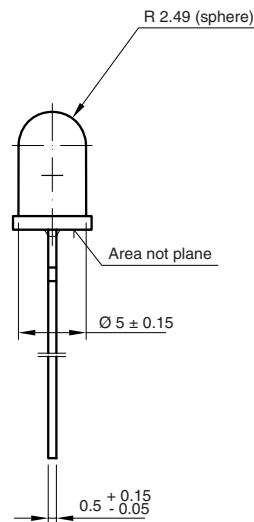
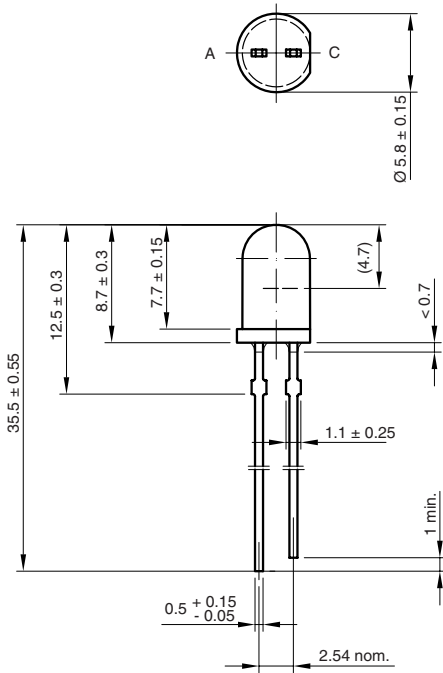


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



6.544-5258.02-4
Issue: 6; 19.05.09
95 10916



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.